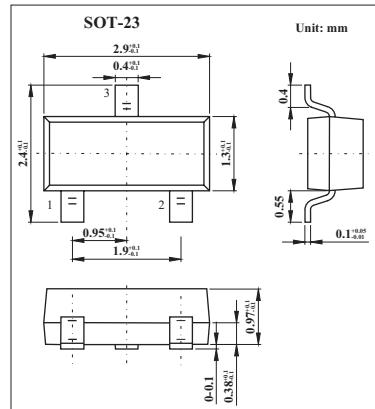


Schottky barrier (double) diodes**BAT754 series****■ Features**

- Ultra high switching speed
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V _R			30	V
Continuous forward current	I _F			200	mA
Repetitive peak forward current	I _{FRM}	t _p < 1 s; δ < 0.5		300	mA
Non-repetitive peak forward current	I _{FSM}	t _p = 8.3 ms half sinewave; JEDEC method		600	mA
Storage temperature	T _{stg}		-65	+150	°C
Junction temperature	T _j			125	°C
Operating ambient temperature	T _{amb}		-65	+125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage	V _F	I _F = 0.1 mA		200	mV
		I _F = 1 mA		260	mV
		I _F = 10 mA		340	mV
		I _F = 30 mA		420	mV
		I _F = 100 mA	600		mV
Reverse current	I _R	V _R = 25 V; Note 1		2	µ A
Diode capacitance	C _d	f = 1 MHz; V _R = 1 V		10	pF

Note

1. Pulse test: t_p < 300 µ s; δ ≤ 0.02.**■ Marking**

Type	BAT754	BAT754A	BAT754C	BAT754S
Marking	2K	2L	2M	2N